Inverting Octal 3-STATE Buffer

MM74HC240

SOIC−20 WB
CASE 751D−05

TSSOP−20 WB
CASE 948E

General Description

The MM74HC240 3−STATE buffer utilizes advanced silicon−gate CMOS technology. It possesses high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits achieve speeds comparable to low power Schottky devices, while retaining the advantage of CMOS circuitry, i.e., high noise immunity and low power consumption. It has a fanout of 15 LS−TTL equivalent inputs.

The MM74HC240 is an inverting buffer and has two active LOW enables ($1\overline{G}$ and $2\overline{G}$). Each enable independently controls 4 buffers.

All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical Propagation Delay: 12 ns
- 3−STATE Outputs for Connection to System Buses
- Wide Power Supply Range: 2–6 V
- Low Quiescent Supply Current: 160 μA (74 Series)
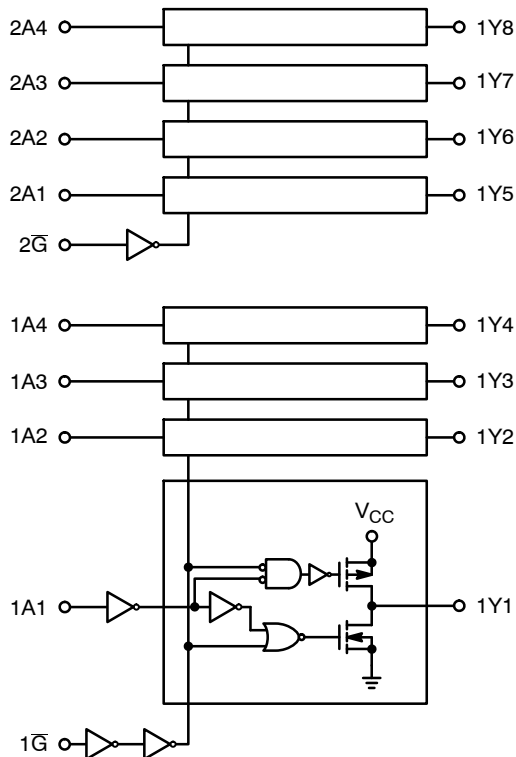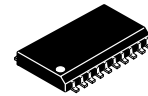- Output Current: 6 mA
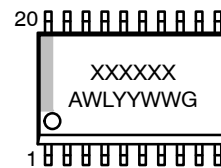- These are Pb−Free Devices

MARKING DIAGRAMS

(SOIC−20 WB)
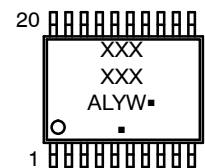
(TSSOP−20 WB)

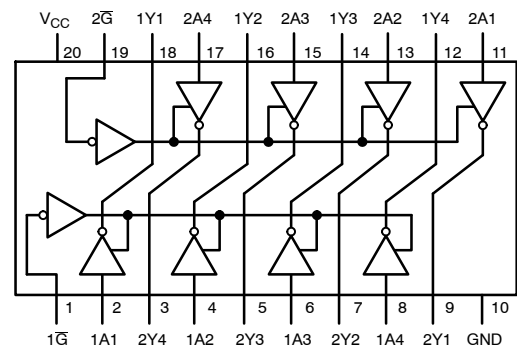|	
XXXXXX	= Specific Device Code
A	= Assembly Location
L/WL	= Wafer Lot
Y/YY	= Year
W/WW	= Work Week
▪ or G	= Pb−Free Package

(Note: Microdot may be in either location)

CONNECTION DIAGRAM

(Top View)

TRUTH TABLE

$1\overline{G}$	1A	1Y	$2\overline{G}$	2A	2Y
L	L	H	L	L	H
L	H	H	L	H	H
H	L	Z	H	L	Z
H	H	Z	H	H	Z

H = HIGH Level
L = LOW Level
Z = HIGH Impedance

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

Figure 1. Logic Diagram

MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	−0.5 to +6.5	V
V_{IN}	DC Input Voltage	−0.5 to V_{CC} + 0.5	V
V_{OUT}	DC Output Voltage	−0.5 to V_{CC} + 0.5	V
I_{IK}, I_{OK}	Clamp Diode Current	±20	mA
I_{OUT}	DC Output Current, per Pin	±35	mA
I_{CC}	DC VCC or GND Current, per Pin	±70	mA
T_{STG}	Storage Temperature Range	−65 to +150	°C
P_D	Power Dissipation SOIC TSSOP	1302 833	mW
T_L	Lead Temperature (Soldering 10 seconds)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Unless otherwise specified all voltages are referenced to ground.

RECOMMENDED OPERATIONG CONDITIONS (Note 1)

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply Voltage	2	6	V
V_{IN}, V_{OUT}	DC Input or Output Voltage	0	V_{CC}	V
T_A	Operating Temperature Range	−55	+125	°C
t_r, t_f	Input Rise or Fall Times V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	− − −	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Note 2)

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C Typ	−40°C ≤ T_A ≤ 85°C Guaranteed Limits	−55°C ≤ T_A ≤ 125°C Guaranteed Limits		Unit
V_{IH}	Minimum HIGH Level Input Voltage		2.0 4.5 6.0	− − −	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum LOW Level Input Voltage		2.0 4.5 6.0	− − −	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
V_{OH}	Minimum HIGH Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $|I_{OUT}|$ ≤ 20 μA	2.0 4.5 6.0	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{IN} = V_{IH} or V_{IL} $|I_{OUT}|$ ≤ 6.0 mA $|I_{OUT}|$ ≤ 7.8 mA	4.5 6.0	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
V_{OL}	Maximum LOW Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $|I_{OUT}|$ ≤ 20 μA	2.0 4.5 6.0	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} $|I_{OUT}|$ ≤ 6.0 mA $|I_{OUT}|$ ≤ 7.8 mA	4.5 6.0	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0	−	±0.1	±1.0	±1.0	μA

MM74HC240

DC ELECTRICAL CHARACTERISTICS (Note 2) (continued)

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C Typ	T_A = 25°C Guaranteed Limits	−40°C ≤ T_A ≤ 85°C	−55°C ≤ T_A ≤ 125°C	Unit
I_{OZ}	Maximum 3−STATE Output Leakage Current	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND $\overline{G}$ = V_{IH}, G = V_{IL}	6.0	−	±0.5	±5	±10	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0	−	8.0	80	160	μA

2. For a power supply of 5 V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5 V. Thus the 4.5 V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5 V and 4.5 V respectively. (The V_{IH} value at 5.5 V is 3.85 V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0 V values should be used.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Unit
t_{PHL}, t_{PLH}	Maximum Propagation Delay	C_L = 45 pF	12	18	ns
t_{PZH}, t_{PZL}	Maximum Enable Delay to Active Output	R_L = 1 kΩ, C_L = 45 pF	14	28	ns
t_{PHZ}, t_{PLZ}	Maximum Disable Delay from Active Output	R_L = 1 kΩ, C_L = 5 pF	13	25	ns

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.0 V to 6.0 V, C_L = 50 pF, t_r = t_f = 6 ns (unless otherwise specified))

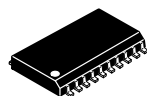| Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C Typ	T_A = 25°C Guaranteed Limits	−40°C ≤ T_A ≤ 85°C	−55°C ≤ T_A ≤ 125°C	Unit
t_{PHL}, t_{PLH}	Maximum Propagation Delay	C_L = 50 pF C_L = 150 pF	2.0 2.0	55 80	100 150	126 190	149 224	ns
		C_L = 50 pF C_L = 150 pF	4.5 4.5	12 22	20 30	25 38	30 45	ns
		C_L = 50 pF C_L = 150 pF	6.0 6.0	11 28	17 26	21 32	25 38	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time	R_L = 1 kΩ C_L = 50 pF C_L = 150 pF	2.0 2.0	75 100	150 200	189 252	224 298	ns
		C_L = 50 pF C_L = 150 pF	4.5 4.5	15 20	30 40	38 50	45 60	ns
		C_L = 50 pF C_L = 150 pF	6.0 6.0	13 17	26 34	32 43	38 51	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time	R_L = 1 kΩ C_L = 50 pF	2.0 4.5 6.0	75 15 13	150 30 26	189 38 32	224 45 38	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0 4.5 6.0	− − −	60 12 10	75 15 13	90 18 15	ns
C_{PD}	Power Dissipation Capacitance (Note 3)	(per buffer) $\overline{G}$ = V_{IH} $\overline{G}$ = V_{IL}	− −	12 50	− −	− −	− −	pF
C_{IN}	Maximum Input Capacitance		−	5	10	10	10	pF
C_{OUT}	Maximum Output Capacitance		−	10	20	20	20	pF

3. C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \cdot V_{CC}^2 \cdot f + I_{CC} \cdot V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \cdot V_{CC} \cdot f + I_{CC}$.

ORDERING INFORMATION

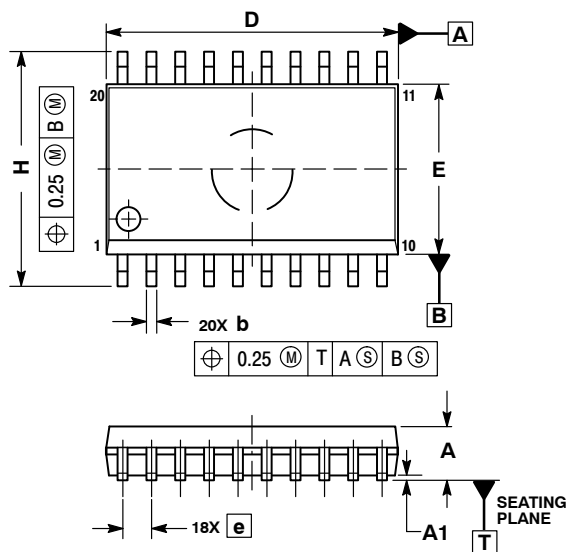| Device	Marking	Package	Shipping†
MM74HC240WM	HC240A	SOIC−20 WB (Pb−Free)	38 Units / Tube
MM74HC240WMX	HC240A	SOIC−20 WB (Pb−Free)	1000 Units / Tape & Reel
MM74HC240MTCX	HC 240A	TSSOP−20 WB (Pb−Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

onsemi

SCALE 1:1

SOIC−20 WB
CASE 751D−05
ISSUE H

DATE 22 APR 2015

D

20   11

H

0.25 Ⓜ B Ⓜ

1   10

20X **b**

⊕ 0.25 Ⓜ T A Ⓢ B Ⓢ

A

18X **e**

A1

SEATING
PLANE

Ⓣ

θ

h X 45°

L

c

NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

**RECOMMENDED
SOLDERING FOOTPRINT***

20X
0.52

20X
1.30

20   11

11.00

1   10

1.27
PITCH
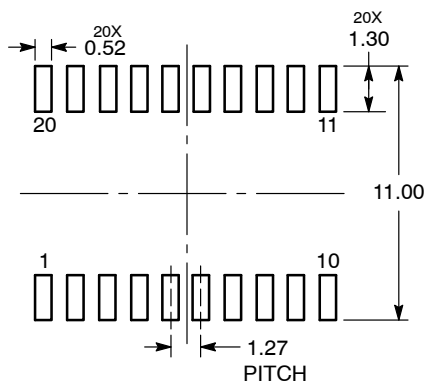
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***

20

XXXXXXXXXX
XXXXXXXXXX
AWLYYWWG

1
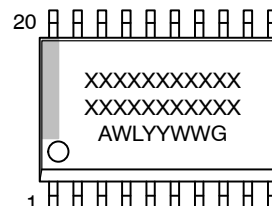
XXXXX = Specific Device Code
A   = Assembly Location
WL   = Wafer Lot
YY   = Year
WW   = Work Week
G   = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42343B	
DESCRIPTION:	SOIC−20 WB	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical–documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

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